

## FQPF5N90C-VB Datasheet

### N-Channel 900 V (D-S) Super Junction Power MOSFET

| PRODUCT SUMMARY           |                        |     |
|---------------------------|------------------------|-----|
| $V_{DS}$ (V)              | 900                    |     |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 10\text{ V}$ | 1.2 |
| $Q_g$ (Max.) (nC)         | 200                    |     |
| $Q_{gs}$ (nC)             | 24                     |     |
| $Q_{gd}$ (nC)             | 110                    |     |
| Configuration             | Single                 |     |

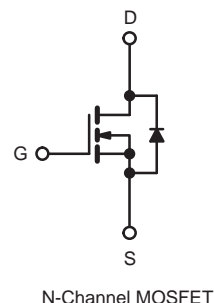
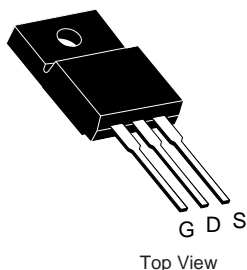
#### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Compliant to RoHS Directive 2002/95/EC



Available  
**RoHS\***  
 COMPLIANT

TO-220 FULLPAK



| ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted) |                                  |                |                                   |                     |
|---|----------------------------------|----------------|-----------------------------------|---------------------|
| PARAMETER   |                                  | SYMBOL         | LIMIT                             | UNIT                |
| Drain-Source Voltage  |                                  | $V_{DS}$       | 900                               | V                   |
| Gate-Source Voltage   |                                  | $V_{GS}$       | $\pm 20$                          |                     |
| Continuous Drain Current  | $V_{GS}$ at 10 V                 | $I_D$          | $T_C = 25\text{ }^\circ\text{C}$  | A                   |
|   |                                  |                | $T_C = 100\text{ }^\circ\text{C}$ |                     |
| Pulsed Drain Current <sup>a</sup>   |                                  | $I_{DM}$       | 21                                |                     |
| Linear Derating Factor  |                                  |                | 1.5                               | W/ $^\circ\text{C}$ |
| Single Pulse Avalanche Energy <sup>b</sup>  |                                  | $E_{AS}$       | 770                               | mJ                  |
| Repetitive Avalanche Current <sup>a</sup>   |                                  | $I_{AR}$       | 7.8                               | A                   |
| Repetitive Avalanche Energy <sup>a</sup>  |                                  | $E_{AR}$       | 19                                | mJ                  |
| Maximum Power Dissipation   | $T_C = 25\text{ }^\circ\text{C}$ | $P_D$          | 190                               | W                   |
| Peak Diode Recovery $dV/dt$ <sup>c</sup>  |                                  | $dV/dt$        | 2.0                               | V/ns                |
| Operating Junction and Storage Temperature Range                                      |                                  | $T_J, T_{stg}$ | - 55 to + 150                     | $^\circ\text{C}$    |
| Soldering Recommendations (Peak Temperature)  | for 10 s                         |                | 300 <sup>d</sup>                  |                     |
| Mounting Torque   | 6-32 or M3 screw                 |                | 10                                | lbf · in            |
|   |                                  |                | 1.1                               | N · m               |

#### Notes

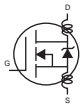

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b.  $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 23\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 7.8\text{ A}$  (see fig. 12).  
 c.  $I_{SD} \leq 7.8\text{ A}$ ,  $dI/dt \leq 140\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq 600\text{ V}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .  
 d. 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

| PARAMETER                           | SYMBOL     | TYP. | MAX. | UNIT |
|-------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient         | $R_{thJA}$ | -    | 40   | °C/W |
| Case-to-Sink, Flat, Greased Surface | $R_{thCS}$ | 0.24 | -    |      |
| Maximum Junction-to-Case (Drain)    | $R_{thJC}$ | -    | 0.65 |      |

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER                                 | SYMBOL              | TEST CONDITIONS   |  | MIN. | TYP. | MAX.      | UNIT                |
|---|---------------------|---|--|------|------|-----------|---------------------|
| Static                                    |                     |   |  |      |      |           |                     |
| Drain-Source Breakdown Voltage            | $V_{DS}$            | $V_{GS} = 0\text{ V}$ , $I_D = 250\text{ }\mu\text{A}$  |  | 900  | -    | -         | V                   |
| $V_{DS}$ Temperature Coefficient          | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$   |  | -    | 0.98 | -         | V/ $^\circ\text{C}$ |
| Gate-Source Threshold Voltage             | $V_{GS(th)}$        | $V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$  |  | 2.0  | -    | 4.0       | V                   |
| Gate-Source Leakage                       | $I_{GSS}$           | $V_{GS} = \pm 20\text{ V}$  |  | -    | -    | $\pm 100$ | nA                  |
| Zero Gate Voltage Drain Current           | $I_{DSS}$           | $V_{DS} = 800\text{ V}$ , $V_{GS} = 0\text{ V}$   |  | -    | -    | 100       | $\mu\text{A}$       |
|   |                     | $V_{DS} = 640\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 125\text{ }^\circ\text{C}$   |  | -    | -    | 500       |                     |
| Drain-Source On-State Resistance          | $R_{DS(on)}$        | $V_{GS} = 10\text{ V}$  | $I_D = 3.7\text{ A}^b$   | -    | 1.2  | -         | $\Omega$            |
| Forward Transconductance                  | $g_{fs}$            | $V_{DS} = 100\text{ V}$ , $I_D = 3.7\text{ A}^b$  |  | 5.6  | -    | -         | S                   |
| Dynamic                                   |                     |   |  |      |      |           |                     |
| Input Capacitance                         | $C_{iss}$           | $V_{GS} = 0\text{ V}$ ,<br>$V_{DS} = 25\text{ V}$ ,<br>$f = 1.0\text{ MHz}$ , see fig. 5  |  | -    | 3100 | -         | pF                  |
| Output Capacitance                        | $C_{oss}$           |   |  | -    | 800  | -         |                     |
| Reverse Transfer Capacitance              | $C_{rss}$           |   |  | -    | 490  | -         |                     |
| Total Gate Charge                         | $Q_g$               | $V_{GS} = 10\text{ V}$  | $I_D = 3.8\text{ A}$ , $V_{DS} = 400\text{ V}$ ,<br>see fig. 6 and 13 <sup>b</sup> | -    | -    | 200       | nC                  |
| Gate-Source Charge                        | $Q_{gs}$            |   |  | -    | -    | 24        |                     |
| Gate-Drain Charge                         | $Q_{gd}$            |   |  | -    | -    | 110       |                     |
| Turn-On Delay Time                        | $t_{d(on)}$         | $V_{DD} = 400\text{ V}$ , $I_D = 3.8\text{ A}$ ,<br>$R_g = 6.2\text{ }\Omega$ , $R_D = 52\text{ }\Omega$<br>see fig. 10 <sup>b</sup>                                |  | -    | 19   | -         | ns                  |
| Rise Time                                 | $t_r$               |   |  | -    | 38   | -         |                     |
| Turn-Off Delay Time                       | $t_{d(off)}$        |   |  | -    | 120  | -         |                     |
| Fall Time                                 | $t_f$               |   |  | -    | 39   | -         |                     |
| Internal Drain Inductance                 | $L_D$               | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact<br> |  | -    | 5.0  | -         | nH                  |
| Internal Source Inductance                | $L_S$               |   |  | -    | 13   | -         |                     |
| Drain-Source Body Diode Characteristics   |                     |   |  |      |      |           |                     |
| Continuous Source-Drain Diode Current     | $I_S$               | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode<br>   |  | -    | -    | 5.0       | A                   |
| Pulsed Diode Forward Current <sup>a</sup> | $I_{SM}$            |   |  | -    | -    | 21        |                     |
| Body Diode Voltage                        | $V_{SD}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_S = 3.8\text{ A}$ , $V_{GS} = 0\text{ V}^b$   |  | -    | -    | 1.8       | V                   |
| Body Diode Reverse Recovery Time          | $t_{rr}$            | $T_J = 25\text{ }^\circ\text{C}$ , $I_F = 3.8\text{ A}$ ,<br>$di/dt = 100\text{ A}/\mu\text{s}^b$   |  | -    | 650  | 980       | ns                  |
| Body Diode Reverse Recovery Charge        | $Q_{rr}$            |   |  | -    | 3.8  | 5.7       | $\mu\text{C}$       |
| Forward Turn-On Time                      | $t_{on}$            | Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )   |  |      |      |           |                     |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
 b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^{\circ}\text{C}$

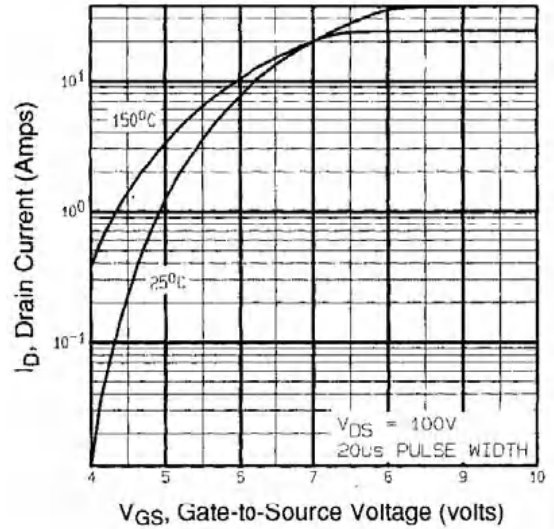


Fig. 3 - Typical Transfer Characteristics



Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^{\circ}\text{C}$

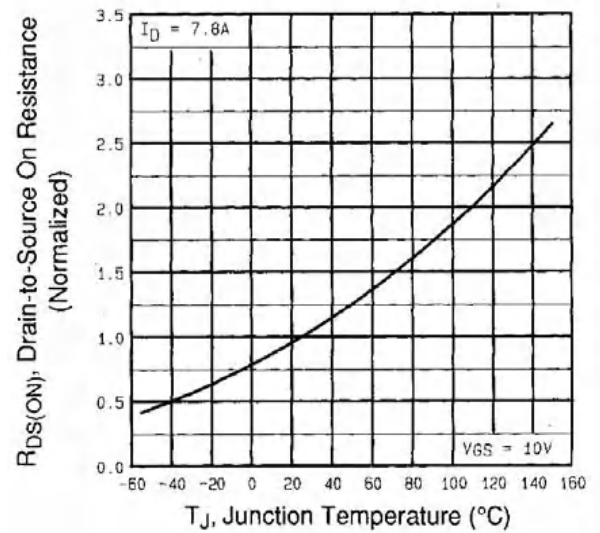


Fig. 4 - Normalized On-Resistance vs. Temperature



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature

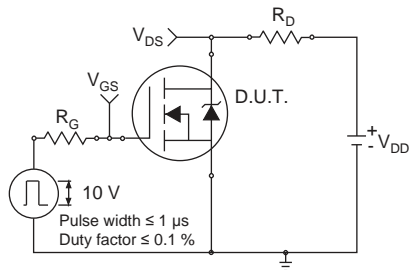


Fig. 10a - Switching Time Test Circuit

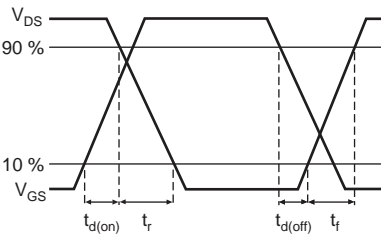


Fig. 10b - Switching Time Waveforms

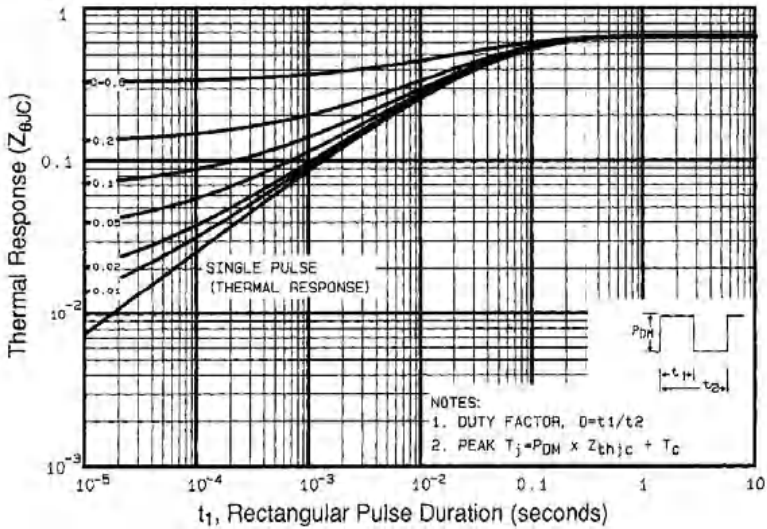


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit

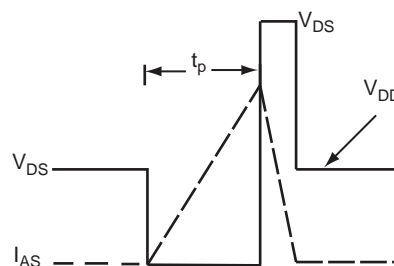


Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

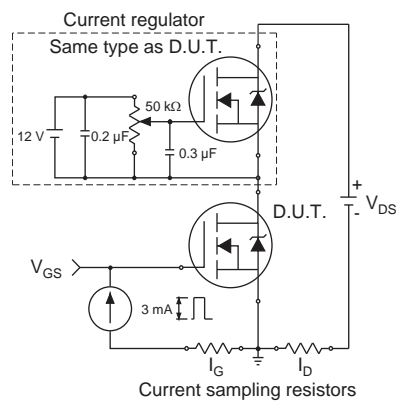


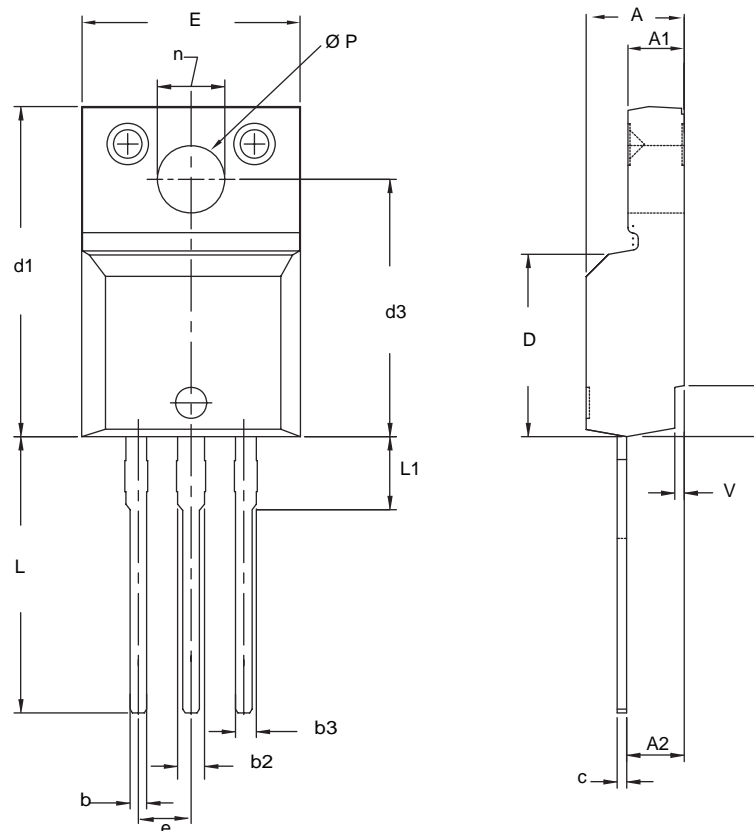
Fig. 13b - Gate Charge Test Circuit



**Note**

a.  $V_{GS} = 5\text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

**TO-220 FULLPAK (HIGH VOLTAGE)**

| DIM. | MILLIMETERS |        | INCHES    |       |
|------|-------------|--------|-----------|-------|
|      | MIN.        | MAX.   | MIN.      | MAX.  |
| A    | 4.570       | 4.830  | 0.180     | 0.190 |
| A1   | 2.570       | 2.830  | 0.101     | 0.111 |
| A2   | 2.510       | 2.850  | 0.099     | 0.112 |
| b    | 0.622       | 0.890  | 0.024     | 0.035 |
| b2   | 1.229       | 1.400  | 0.048     | 0.055 |
| b3   | 1.229       | 1.400  | 0.048     | 0.055 |
| c    | 0.440       | 0.629  | 0.017     | 0.025 |
| D    | 8.650       | 9.800  | 0.341     | 0.386 |
| d1   | 15.88       | 16.120 | 0.622     | 0.635 |
| d3   | 12.300      | 12.920 | 0.484     | 0.509 |
| E    | 10.360      | 10.630 | 0.408     | 0.419 |
| e    | 2.54 BSC    |        | 0.100 BSC |       |
| L    | 13.200      | 13.730 | 0.520     | 0.541 |
| L1   | 3.100       | 3.500  | 0.122     | 0.138 |
| n    | 6.050       | 6.150  | 0.238     | 0.242 |
| Ø P  | 3.050       | 3.450  | 0.120     | 0.136 |
| u    | 2.400       | 2.500  | 0.094     | 0.098 |
| v    | 0.400       | 0.500  | 0.016     | 0.020 |

ECN: X09-0126-Rev. B, 26-Oct-09  
DWG: 5972

**Notes**

1. To be used only for process drawing.
2. These dimensions apply to all TO-220, FULLPAK leadframe versions 3 leads.
3. All critical dimensions should C meet  $C_{pk} > 1.33$ .
4. All dimensions include burrs and plating thickness.
5. No chipping or package damage.



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